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K64L5111A

- Light Emitting Diode
- Orchid color tone
- InGaN structure
- 5 mm clear epoxy package



Description

K64L5111 is an **InGaN** based LED with a phosphorous coating, emitting an **orchid light** of high luminous intensity (8.4 cd). It comes in a hermetically sealed clear 5 mm UV resistant epoxy resin.

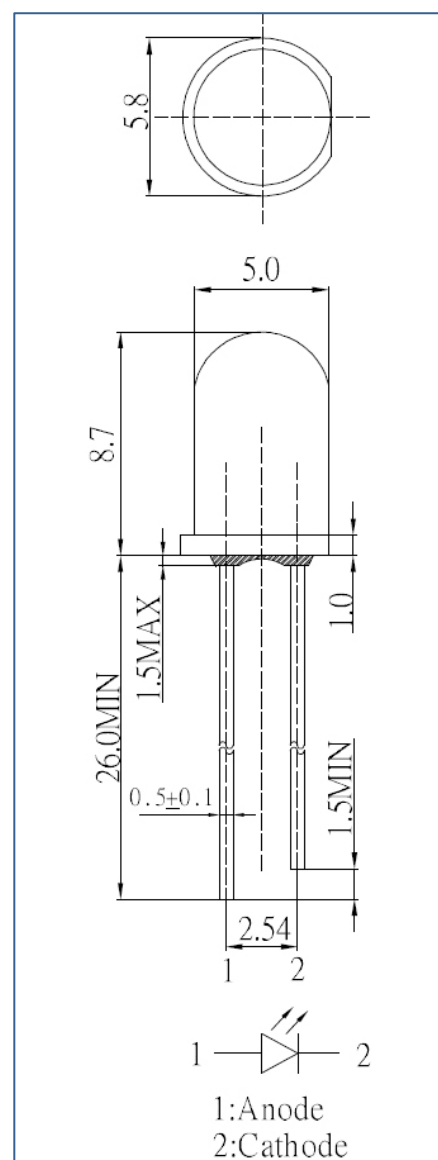
Maximum Rating ($T_{CASE} = 25^{\circ}C$)

Parameter	Symbol	Values		Unit
		Min.	Max.	
Power Dissipation, DC	P_D		102	mW
DC Forward Current*	I_F		30	mA
Pulse Forward Current*	I_{FP}		100	mA
Reverse Voltage	V_R		5.0	V
Operating Temperature	T_{OPR}	- 30	+ 85	$^{\circ}C$
Storage Temperature	T_{STG}	- 40	+ 100	$^{\circ}C$
Soldering Temperature (max 5s)	T_{SOL}		+ 260	$^{\circ}C$

* Duty cycle max. 10%, Pulse width max 10ms

Electro-Optical Characteristics ($T_{CASE} = 25^{\circ}C$, $I_F = 20$ mA)

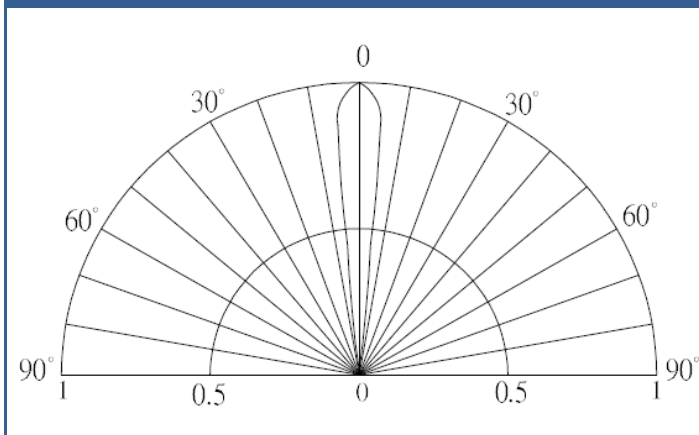
Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Chromaticity Coordinates	x		0.25		
	y		0.14		
Forward Voltage	V_F	2.7	2.9	3.4	V
Reverse Current ($V_R = 5V$)	V_R			10	μA
Luminous Intensity	I_V	7.0	8.4		cd
Viewing Half Angle	$\Theta_{1/2}$		7.5		deg.



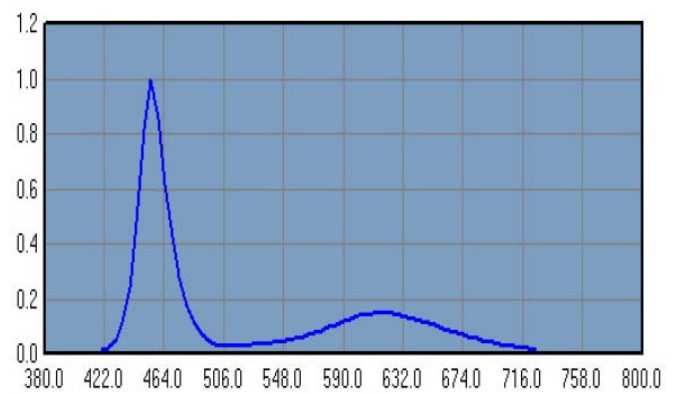


Performance Characteristics

Forward Current vs. Forward Voltage



Relative spectral distribution vs. Wavelength



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The above specifications are for reference purpose only and subjected to change without prior notice